

DATA SHEET

74ABT125

Quad buffer (3-State)

Product specification
Supersedes data of 1996 Mar 05
IC23 Data Handbook

1998 Jan 16

Quad buffer (3-State)

74ABT125

FEATURES

- Quad bus interface
- 3-State buffers
- Live insertion/extraction permitted
- Output capability: +64mA/–32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- Power-up 3-State
- Inputs are disabled during 3-State mode

DESCRIPTION

The 74ABT125 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT125 device is a quad buffer that is ideal for driving bus lines. The device features four Output Enables ($\overline{OE}0$, $\overline{OE}1$, $\overline{OE}2$, $\overline{OE}3$), each controlling one of the 3-State outputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS $T_{amb} = 25^{\circ}\text{C}$; $GND = 0V$	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay An to Yn	$C_L = 50\text{pF}$; $V_{CC} = 5V$	2.9	ns
C_{IN}	Input capacitance	$V_I = 0V$ or V_{CC}	4	pF
C_{OUT}	Output capacitance	Outputs disabled; $V_O = 0V$ or V_{CC}	7	pF
I_{CCZ}	Total supply current	Outputs disabled; $V_{CC} = 5.5V$	65	μA

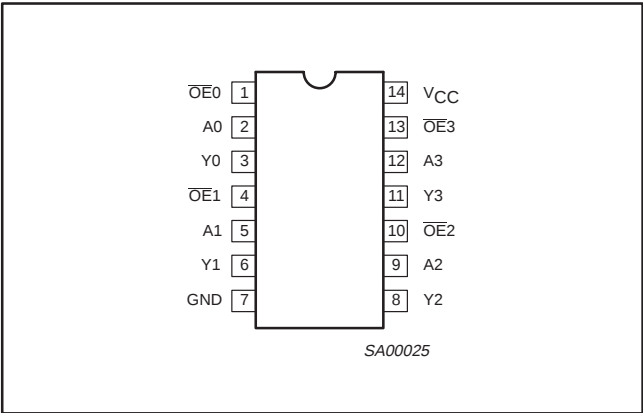
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic DIP	–40°C to +85°C	74ABT125 N	74ABT125 N	SOT27-1
14-Pin plastic SO	–40°C to +85°C	74ABT125 D	74ABT125 D	SOT108-1
14-Pin Plastic SSOP Type II	–40°C to +85°C	74ABT125 DB	74ABT125 DB	SOT337-1
14-Pin Plastic TSSOP Type I	–40°C to +85°C	74ABT125 PW	74ABT125PW DH	SOT402-1

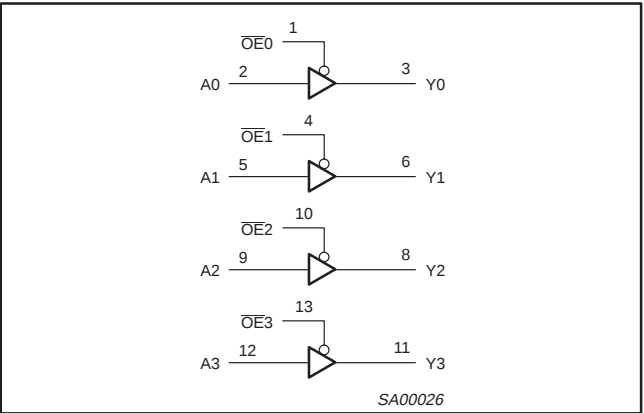
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
2, 5, 9, 12	A0 – A3	Data inputs
3, 6, 8, 11	Y0 – Y3	Data outputs
1, 4, 10, 13	$\overline{OE}0$ – $\overline{OE}3$	Output enable inputs (active-Low)
7	GND	Ground (0V)
14	V_{CC}	Positive supply voltage

PIN CONFIGURATION



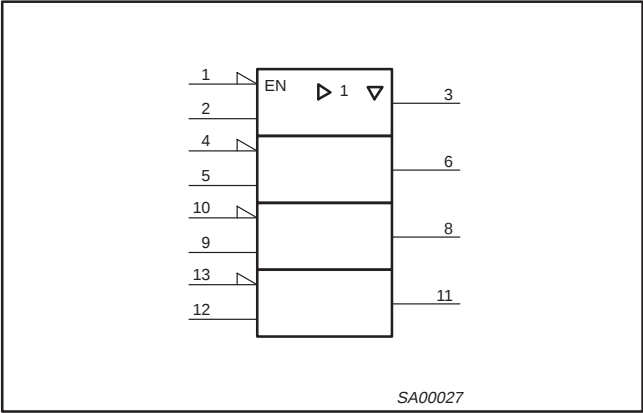
LOGIC SYMBOL



Quad buffer (3-State)

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LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INPUTS		OUTPUTS
$\overline{O}En$	A_n	Y_n
L	L	L
L	H	H
H	X	Z

H = High voltage level
L = Low voltage level
X = Don't care
Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		−0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	−18	mA
V_I	DC input voltage ³		−1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	−50	mA
V_{OUT}	DC output voltage ³	output in Off or High state	−0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	128	mA
T_{stg}	Storage temperature range		−65 to 150	°C

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		MIN	MAX	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Low-level input voltage		0.8	V
I_{OH}	High-level output current		−32	mA
I_{OL}	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_{amb}	Operating free-air temperature range	−40	+85	°C

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DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			T _{amb} = +25°C			T _{amb} = −40°C to +85°C		
			Min	Typ	Max	Min	Max	
V _{IK}	Input clamp voltage	V _{CC} = 4.5V; I _{IK} = −18mA		−0.9	−1.2		−1.2	V
V _{OH}	High-level output voltage	V _{CC} = 4.5V; I _{OH} = −3mA; V _I = V _{IL} or V _{IH}	2.5	2.9		2.5		V
		V _{CC} = 5.0V; I _{OH} = −3mA; V _I = V _{IL} or V _{IH}	3.0	3.4		3.0		V
		V _{CC} = 4.5V; I _{OH} = −32mA; V _I = V _{IL} or V _{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output voltage	V _{CC} = 4.5V; I _{OL} = 64mA; V _I = V _{IL} or V _{IH}		0.35	0.55		0.55	V
I _I	Input leakage current	V _{CC} = 5.5V; V _I = GND or 5.5V		±0.01	±1.0		±1.0	μA
I _{OFF}	Power-off leakage current	V _{CC} = 0.0V; V _O or V _I ≤ 4.5V		±5.0	±100		±100	μA
I _{PU} /I _{PD}	Power-up/down 3-State output current ³	V _{CC} = 2.1V; V _O = 0.5V; V _I GND or V _{CC} ; V _{OE} = Don't care		±5.0	±50		±50	μA
I _{OZH}	3-State output High current	V _{CC} = 5.5V; V _O = 2.7V; V _I = V _{IL} or V _{IH}		1.0	50		50	μA
I _{OZL}	3-State output Low current	V _{CC} = 5.5V; V _O = 0.5V; V _I = V _{IL} or V _{IH}		−1.0	−50		−50	μA
I _{CEX}	Output High leakage current	V _{CC} = 5.5V; V _O = 5.5V; V _I = GND or V _{CC}		5.0	50		50	μA
I _O	Output current ¹	V _{CC} = 5.5V; V _O = 2.5V	−50	−100	−180	−50	−180	mA
I _{CCH}	Quiescent supply current	V _{CC} = 5.5V; Outputs High, V _I = GND or V _{CC}		65	250		250	μA
I _{CCL}		V _{CC} = 5.5V; Outputs Low, V _I = GND or V _{CC}		12	15		30	mA
I _{CCZ}		V _{CC} = 5.5V; Outputs 3-State; V _I = GND or V _{CC}		65	250		50	μA
ΔI _{CC}	Additional supply current per input pin ²	Outputs enabled, one data input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.5	1.5		1.5	mA
		Outputs 3-State, one data input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		50	250		250	μA
		Outputs 3-State, one enable input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.5	1.5		1.5	mA

NOTES:

- Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- This is the increase in supply current for each input at 3.4V.
- This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to 10msec. From V_{CC} = 2.1V to V_{CC} = 5V ± 10% a transition time of up to 100µsec is permitted.

AC CHARACTERISTICS

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF, R_L = 500Ω

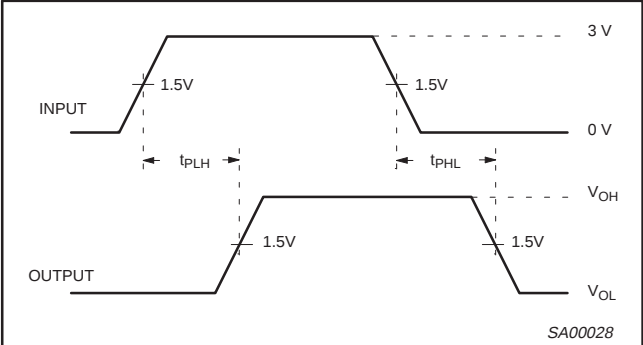
SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT
			T _{amb} = +25°C V _{CC} = +5.0V			T _{amb} = -40°C to +85°C V _{CC} = +5.0V ±0.5V		
			MIN	TYP	MAX	MIN	MAX	
t _{PLH} t _{PHL}	Propagation delay An to Yn	1	1.0 1.0	2.8 3.1	4.1 4.6	1.0 1.0	4.6 4.9	ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	2	1.0 1.0	3.2 4.2	5.0 6.2	1.0 1.0	5.9 6.8	ns
t _{PHZ} t _{PLZ}	Output disable time from High and Low level	2	1.0 1.5	4.1 2.8	5.4 5.0	1.0 1.5	6.2 5.5	ns

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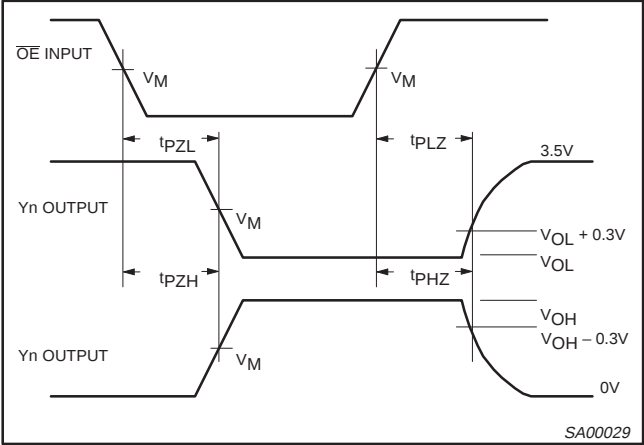
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AC WAVEFORMS

$V_M = 1.5\text{V}$, $V_{IN} = \text{GND to } 3.0\text{V}$

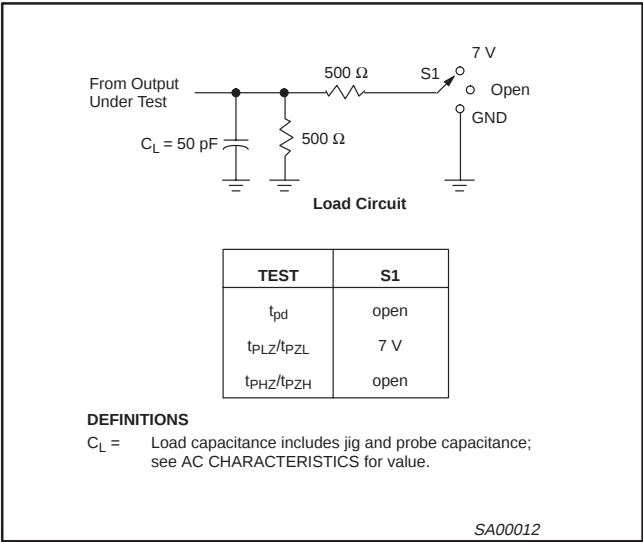


Waveform 1. Waveforms Showing the Input (An) to Output (Yn) Propagation Delays



Waveform 2. Waveforms Showing the 3-State Output Enable and Disable Times

TEST CIRCUIT AND WAVEFORMS

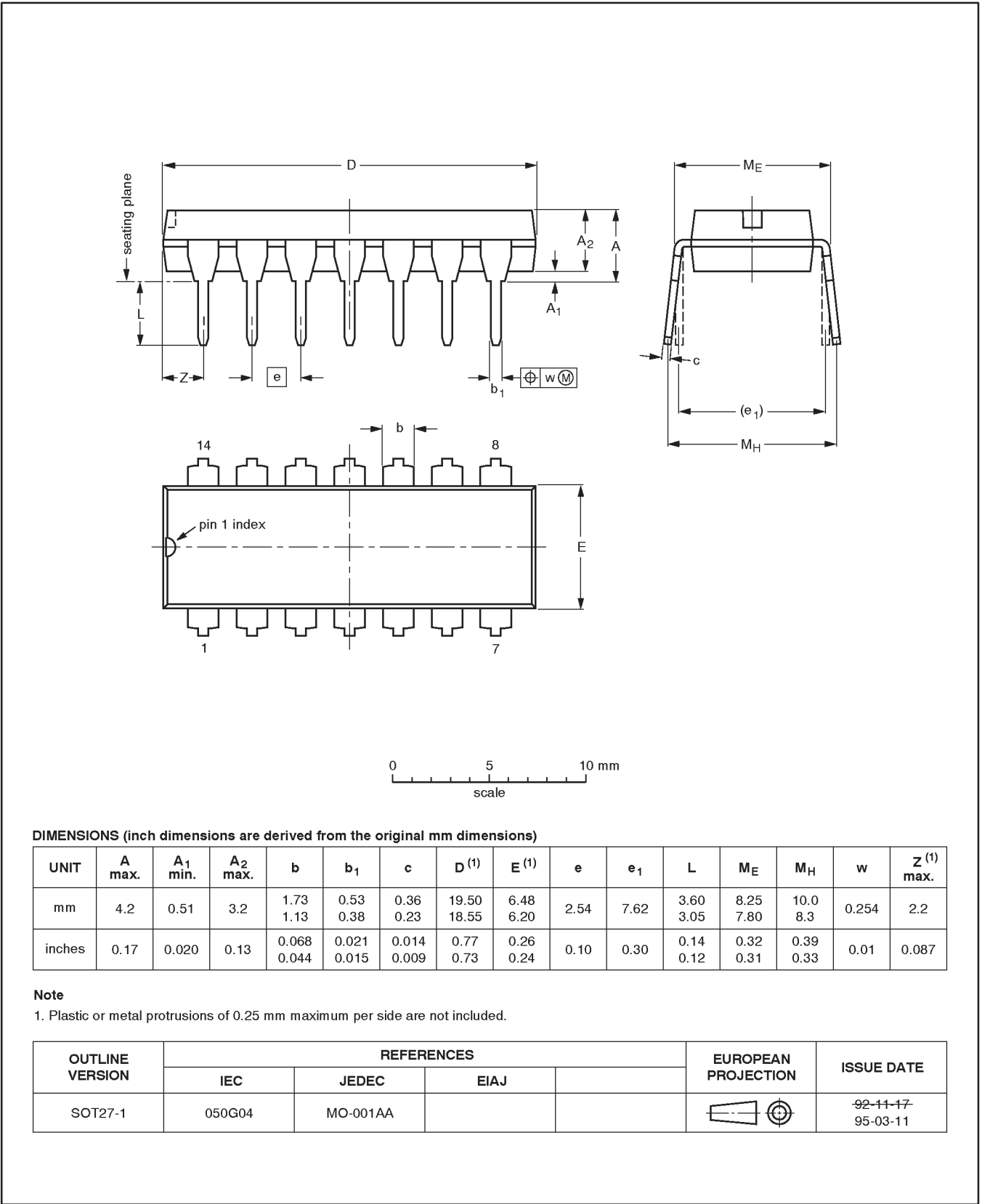


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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

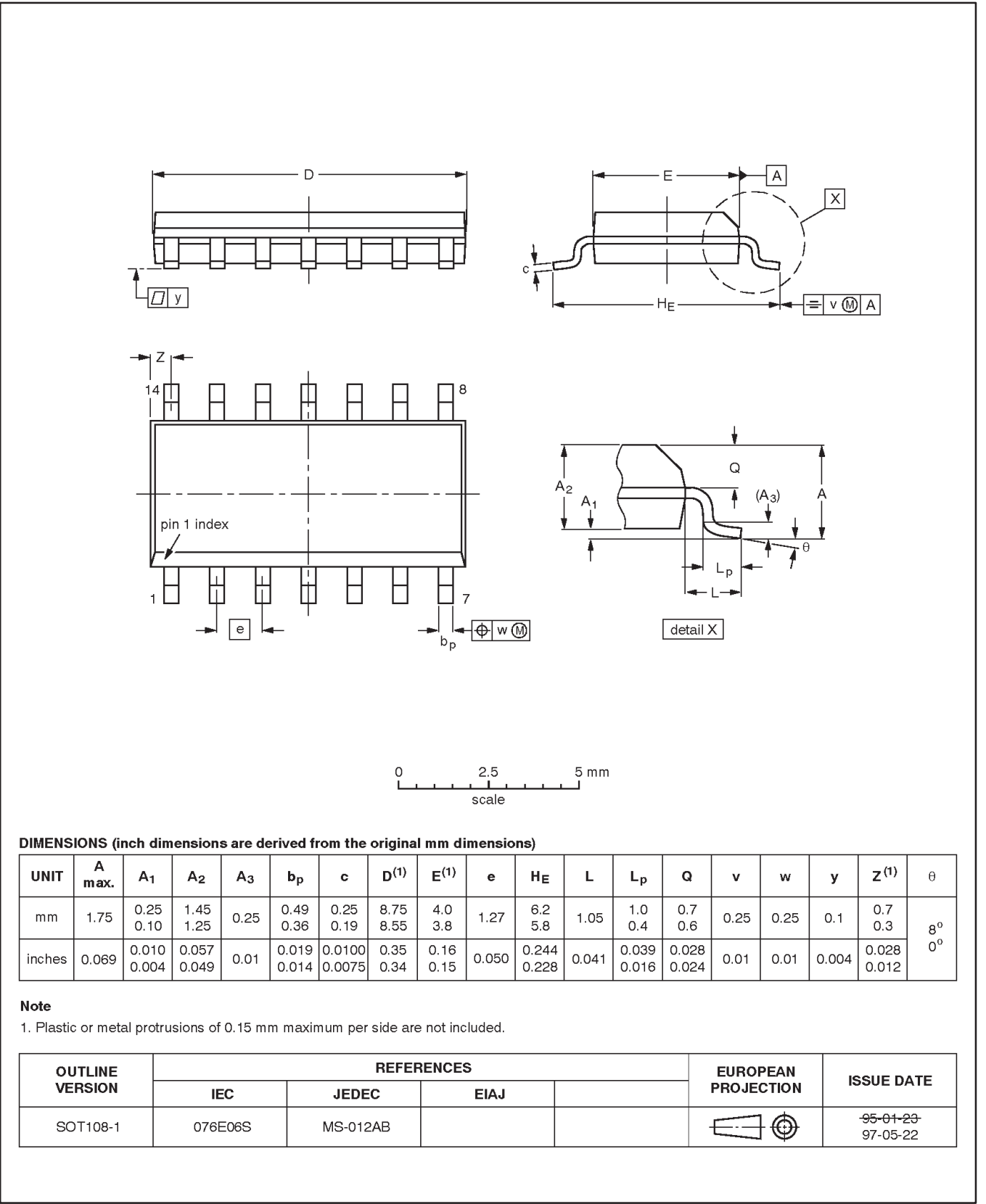


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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

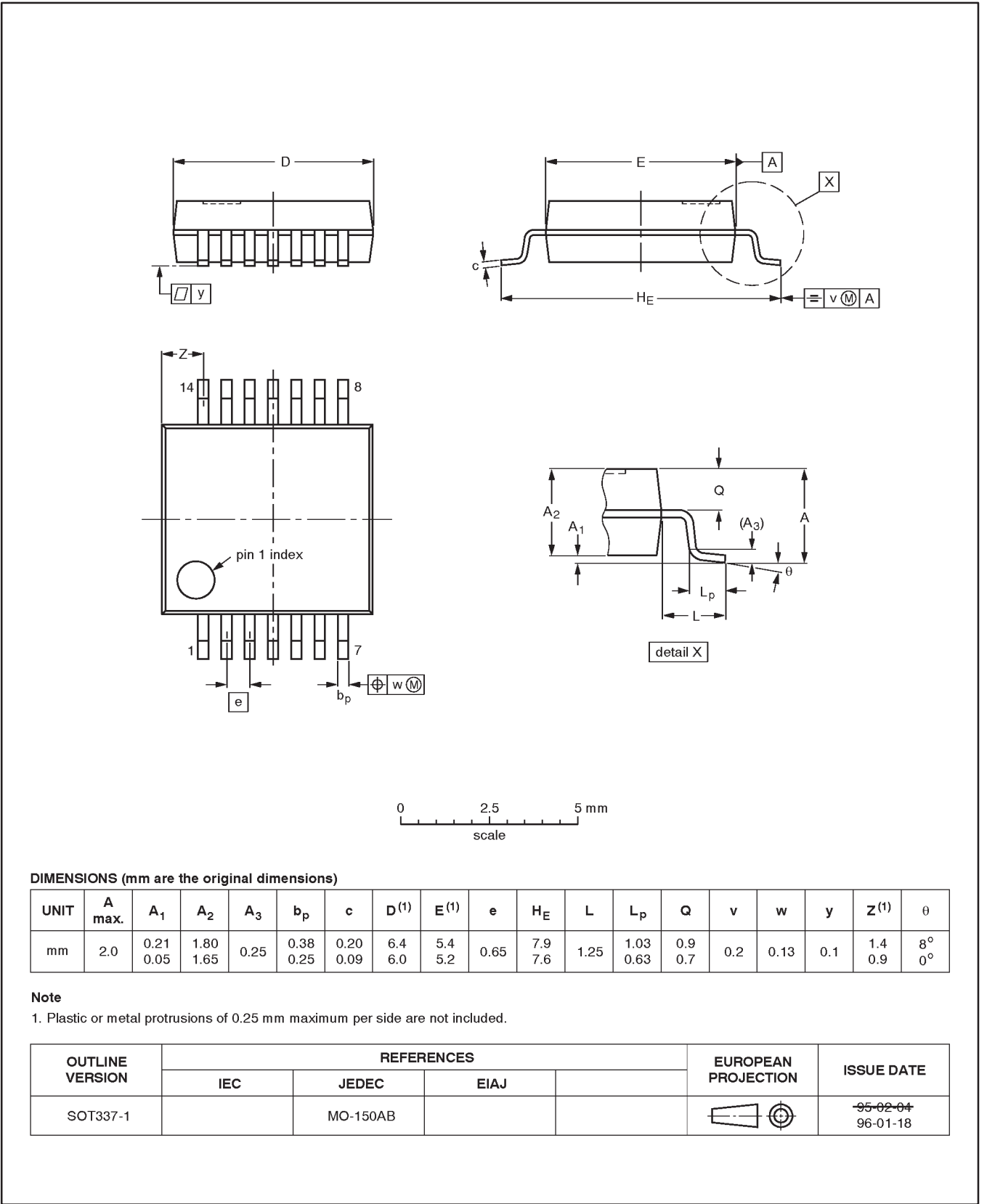


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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

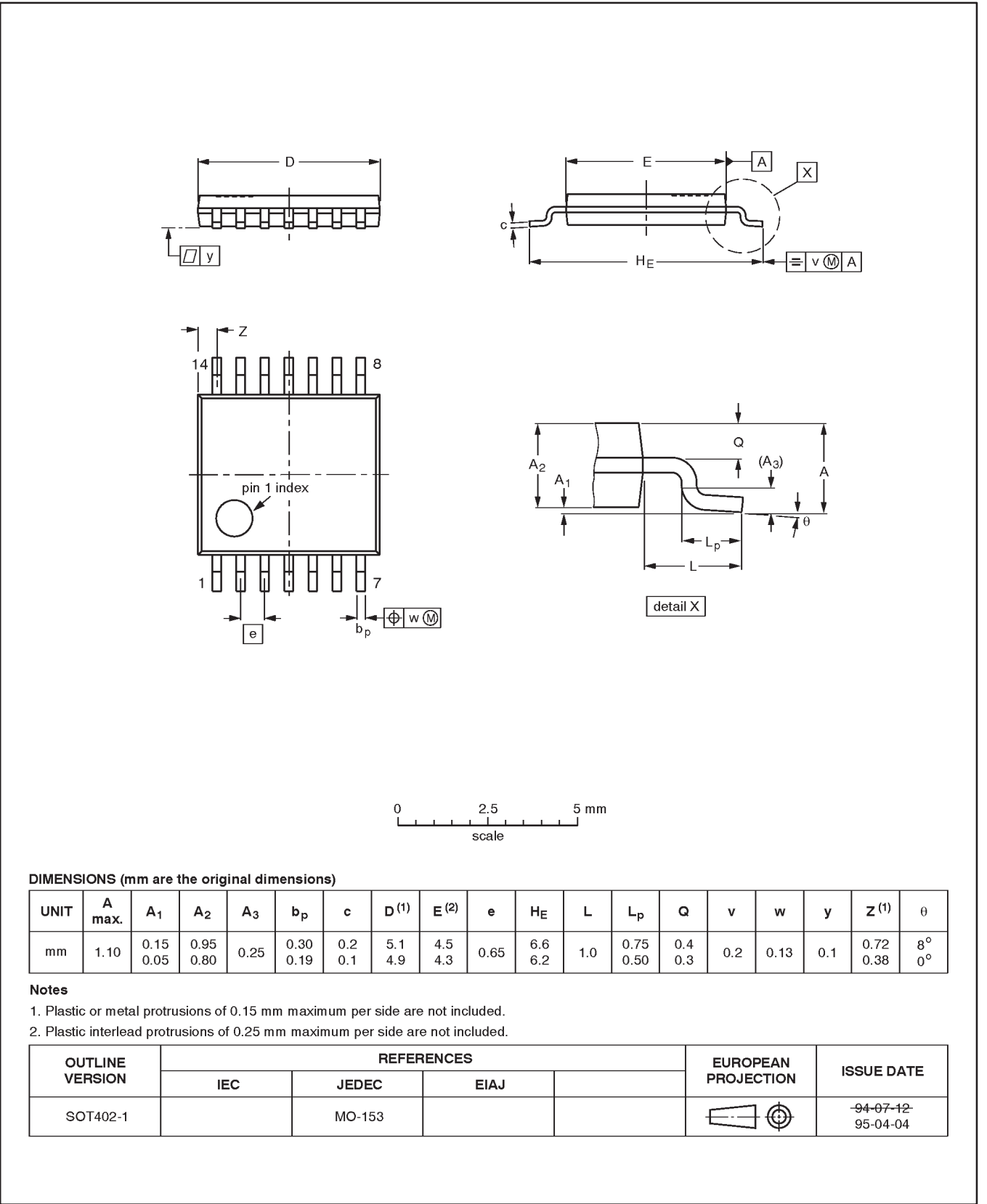


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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



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DEFINITIONS		
Data Sheet Identification	Product Status	Definition
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
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